

Supporting Information

Coaxial Yarn Electrode Based on Hierarchical MoS₂ Nanosheets/Carbon Fiber Tows for Flexible Solid-State Supercapacitors

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Synthesis of MoS₂ NSs

Typically, (NH₄)₆Mo₇O₂₄·4H₂O (0.14 mmol) and CH₄N₂S (2.00 mmol) were respectively dissolved in deionized water under vigorous stirring to form a homogeneous solution. The reaction was conducted at 200 °C for 9 h in an electric oven. After reaction, the samples were cooled to room temperature naturally, washed several times with deionized water and absolute ethanol, and then dried at 80 °C for 6 h under vacuum.

Supporting Figures and some illustrations

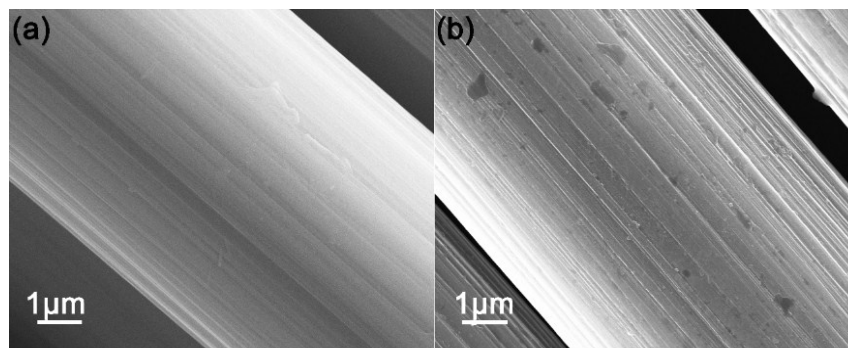


Figure S1. SEM images of a single CF (a) and ACF (b).

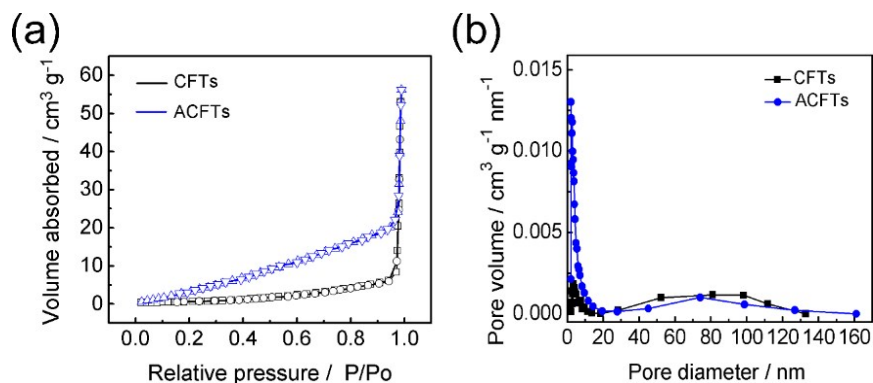


Figure S2. Nitrogen adsorption/desorption isotherms (a) and pore-size distribution (b) of CFTs and ACFTs.

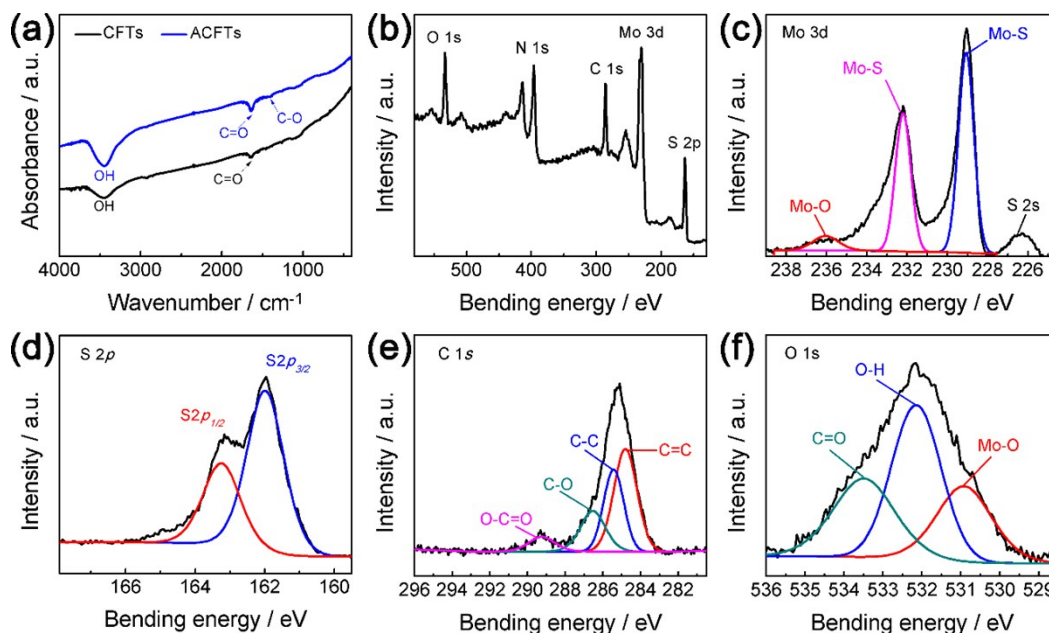


Figure S3. (a) The FTIR spectra of CFTs and ACFTs; (b) Low resolution XPS spectrum of ACFTs/MoS₂; High resolution XPS spectrum of Mo 3d (c), S 2p (d), C 1s (e) and O 1s (f) of ACFTs/MoS₂.

(1) Illustration for XPS spectra in figures S3b-S3f

The oxidation state and chemical composition of the ACFTs/MoS₂ were analyzed by XPS. Wide scan XPS spectra of ACFTs/MoS₂ is shown in Figure S3b. Carbon (C), nitrogen (N), sulfur (S) and molybdenum (Mo) peaks can be observed, in which N element may come from nitrogen-contained precursor in the solution of ((NH₄)₂S₂O₈).¹ As seen in Figure S3c, there are two characteristic peaks at 229.1 and 232.2 eV, which correspond to the Mo 3d_{5/2} and Mo 3d_{3/2} orbitals, respectively, suggesting a Mo (IV) characteristic in MoS₂. The peak at 236.1 eV related to the Mo 3d_{5/2} corresponding to Mo (VI) is in agreement with typical Mo-O bonds,² while the

peak at 226.0 eV can be indexed as S2s. The binding energies located at 162.0 and 163.3 eV are due to S 2p_{3/2} and 2p_{1/2} of MoS₂, respectively (Figure S3d). Above binding energy are all in good agreement with values of MoS₂ crystal reported previously.³ The C1s XPS profile of the ACFTs/MoS₂ (Figure S3e) showed two main strong peaks, corresponding to the sp² C=C and C-C bonds at 284.8 and 286.5 eV. In general, the C1s spectrum of ACFTs showed another two peaks centered at 286.5 and 289.2 eV, which correspond to the binding energy of C-O bonds and O-C=O bonds, respectively.⁴⁻⁷ Therefore, the C1s spectrum of the ACFTs/MoS₂ indicates the oxidation of ACFTs (with oxygen containing functionalized groups). Figure S3f shows the narrow XPS spectrum of O 1s, in which three peaks can be found in the case of ACFTs/MoS₂, with one peak around 531.0 eV relating to the Mo-O bonds and another two peaks around 532.2 and 533.5 eV corresponding to O-H bonds and C=O bonds, respectively. The O 1s peak around 531.0 eV cannot be associated with MoO₃ phase whose peak is expected at 530.6 eV.⁸ The O-H bonds and C=O bonds found in spectrum of O 1s further confirm that the acid treatment can introduce oxygen-containing groups on the surface of CFT. Meanwhile, the weak Mo-O bonds (531.0 eV) and Mo-O bonds (236.1 eV) seen in XPS spectrum of Mo 3d both indicate that the existence of oxygen element plays a critical role in connecting MoS₂ and carbon fiber through Mo-O-C chemical bond.

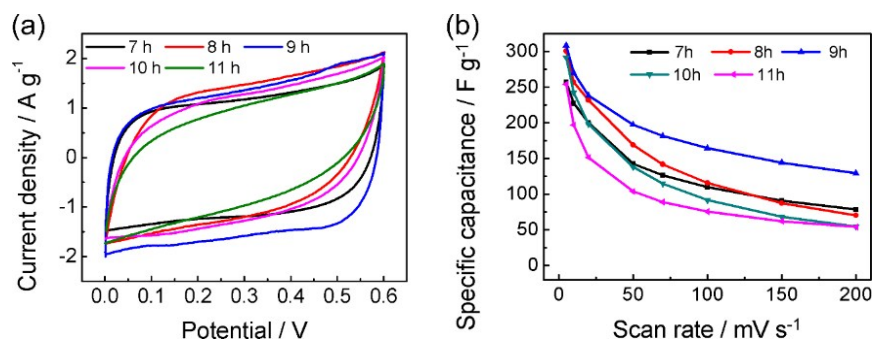


Figure S4. CV performance (a) and plots of specific capacitance vs scan rate (b) of ACFTs/MoS₂ electrode synthesized for different time

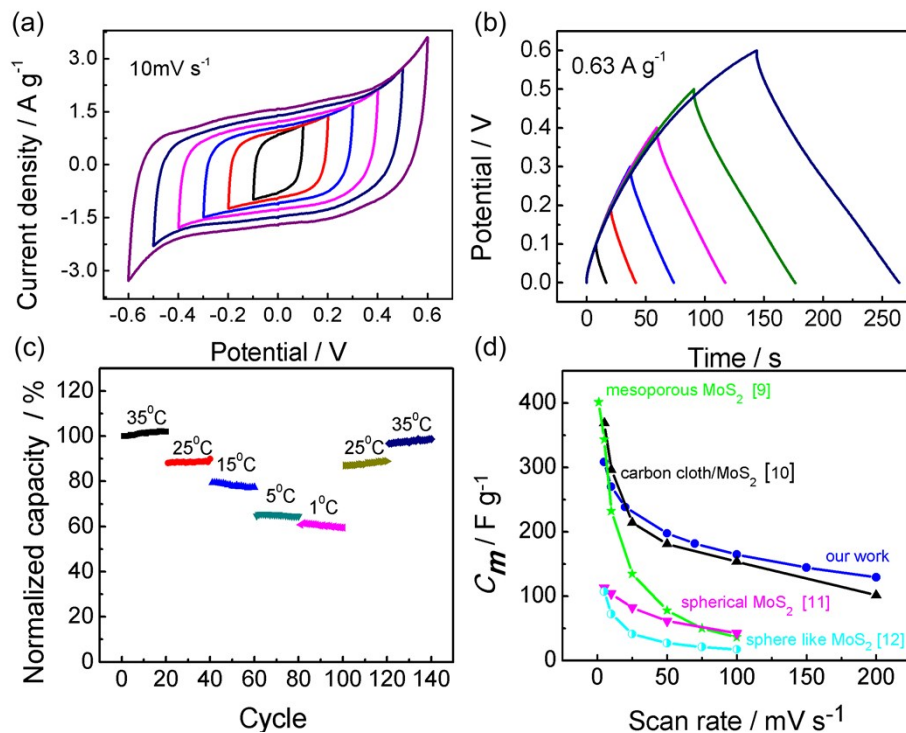


Figure S5 Electrochemical performances of ACFTs/MoS₂ planar pattern SC. (a) CV curves under different voltage windows at 10 mV s⁻¹; (b) GCD performances under different voltage ranges at 0.63 A g⁻¹; (c) Normalized Capacity under different controlling temperatures (c); (d) Comparison of mass specific capacitance of MoS₂-based SC in recent papers.⁹⁻¹²

(2) Illustration for temperature influence on capacitance in figures S5c

The influence of measuring temperature on the electrochemical performances of ACFTs/MoS₂ planar pattern SC is shown in Figure S5c. To get the results, the charging-discharging performance of ACFTs/MoS₂ planar pattern SC was measured at constant current density of 2.21 A g⁻¹, and the ambient temperature was controlled to decrease from initial 35 °C to 1 °C and then recover to 35 °C, and under each temperature, only the SC was charged-discharged twenty times. All the capacities gained under different temperatures was normalized to the initial capacity under 35 °C, and then the normalized capacity could be got. As the temperature decreases from 35 °C to 1 °C, the capacity decreases gradually to 61.2% of its initial value with good stability at each test temperature and recovers to 98.7% of the initial value as the temperature increased to 35 °C, demonstrating that the ambient temperature has an impact on specific capacitance.

Calculation of electrochemical capacitance:

The specific capacitance of electrodes, including mass specific capacitance (C_m) and volumetric specific capacitance (C_v), are calculated according to formulas (1) and (2) reported previously¹³, where C is the measured capacitance (from CV) in the two-electrode configuration, M and V are respectively the mass of MoS₂ nanosheets and volume of the single fiber electrode.

$$C_m = 2C/M \quad (1)$$

$$C_v = 2C/V \quad (2)$$

The mass energy density (E_m), volumetric energy density (E_v), mass power density (P_m) and volumetric power density (P_v) can be obtained according to formulas (3-6) from GCD curves, where t is the discharge time, U represents the potential window.

$$E_m = C_m \times U^2 \times 8^{-1} \times 3.6^{-1} \quad (3)$$

$$E_v = C_v \times U^2 \times 8^{-1} \times 3.6^{-1} \quad (4)$$

$$P_m = E_m \times 3,600 \times t^{-1} \quad (5)$$

$$P_v = E_v \times 3,600 \times t^{-1} \quad (6)$$

Supporting References:

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